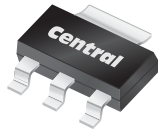


CZTA27

**SURFACE MOUNT SILICON
HIGH VOLTAGE NPN
DARLINGTON TRANSISTOR**



SOT-223 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CZTA27 is a silicon NPN Darlington transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for applications requiring extremely high gain and high voltage.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Collector-Emitter Voltage
Emitter-Base Voltage
Continuous Collector Current
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL		UNITS
V_{CES}	60	V
V_{EBO}	10	V
I_C	500	mA
P_D	2.0	W
T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
θ_{JA}	62.5	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

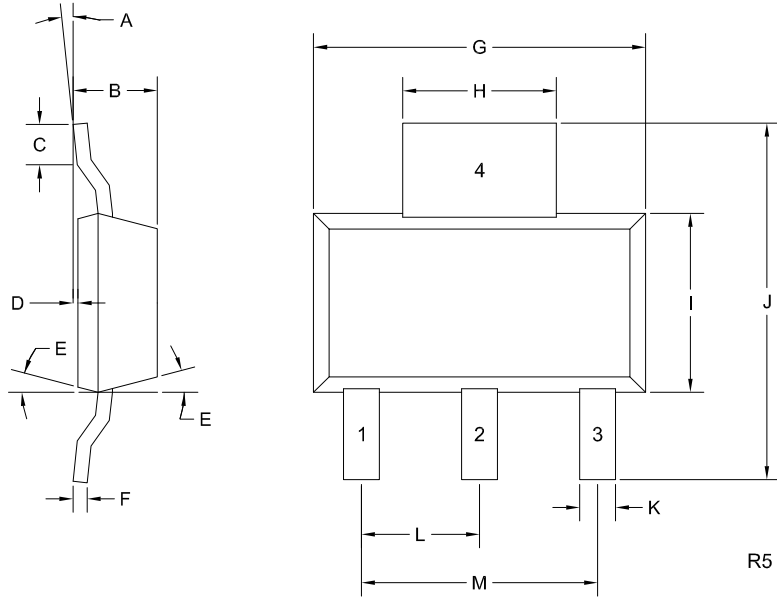
SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CBO}	$V_{CB}=50\text{V}$		100	nA
I_{CES}	$V_{CE}=50\text{V}$		500	nA
I_{EBO}	$V_{EB}=10\text{V}$		100	nA
BV_{CBO}	$I_C=100\mu\text{A}$	60		V
BV_{CES}	$I_C=100\mu\text{A}$	60		V
$V_{CE(SAT)}$	$I_C=100\text{mA}, I_B=0.1\text{mA}$		1.5	V
$V_{BE(ON)}$	$V_{CE}=5.0\text{V}, I_C=100\text{mA}$		2.0	V
h_{FE}	$V_{CE}=5.0\text{V}, I_C=10\text{mA}$	10,000		
h_{FE}	$V_{CE}=5.0\text{V}, I_C=100\text{mA}$	10,000		
f_T	$V_{CE}=5.0\text{V}, I_C=10\text{mA}, f=100\text{MHz}$	125		MHz

R5 (7-May 2019)

CZTA27
SURFACE MOUNT SILICON
HIGH VOLTAGE NPN
DARLINGTON TRANSISTOR



SOT-223 CASE - MECHANICAL OUTLINE



LEAD CODE:

- 1) Base
- 2) Collector
- 3) Emitter
- 4) Collector

MARKING:

FULL PART NUMBER

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0°	10°	0°	10°
B	0.059	0.071	1.50	1.80
C	0.018	---	0.45	---
D	0.000	0.004	0.00	0.10
E	10°		10°	
F	0.009	0.014	0.23	0.35
G	0.248	0.270	6.30	6.85
H	0.114	0.122	2.90	3.10
I	0.130	0.146	3.30	3.70
J	0.264	0.287	6.70	7.30
K	0.024	0.033	0.60	0.85
L	0.091		2.30	
M	0.181		4.60	

SOT-223 (REV: R5)

R5 (7-May 2019)